Preferred Device

# **Darlington Complementary Silicon Power Transistors**

This package is designed for general-purpose amplifier and low frequency switching applications.

#### **Features**

- High DC Current Gain  $h_{FE} = 3500$  (Typ) @  $I_C = 5.0$  Adc
- Collector–Emitter Sustaining Voltage @ 100 mA V<sub>CEO(sus)</sub> = 100 Vdc (Min)
- Monolithic Construction with Built-In Base-Emitter Shunt Resistors
- This is a Pb-Free Device\*

### **MAXIMUM RATINGS** (Note 1)

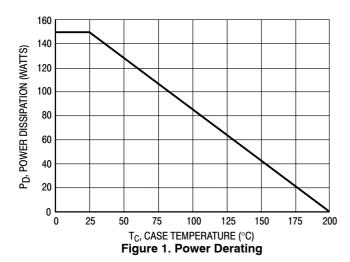
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	100	Vdc
Collector-Base Voltage	V <sub>CB</sub>	100	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current - Continuous Peak	I <sub>C</sub>	12 20	Adc
Base Current	Ι <sub>Β</sub>	0.2	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	150 0.857	W W/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.17	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC Registered Data.

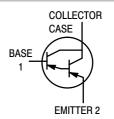




# ON Semiconductor®

http://onsemi.com

# 12 AMPERE COMPLEMENTARY SILICON POWER TRANSISTOR 100 VOLTS, 150 WATTS



### MARKING DIAGRAM





TO-204AA (TO-3) CASE 1-07 STYLE 1

 2N6052
 = Device Code

 G
 = Pb-Free Package

 A
 = Location Code

 YY
 = Year

 WW
 = Work Week

 MEX
 = Country of Orgin

# **ORDERING INFORMATION**

Device	Package	Shipping
2N6052G	TO-3 (Pb-Free)	100 Units/Tray

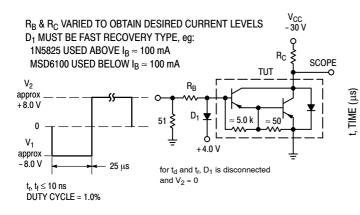
**Preferred** devices are recommended choices for future use and best overall value.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted) (Note 2)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•	•	•	•
Collector-Emitter Sustaining Voltage (Note	e 3) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	100	-	Vdc
Collector Cutoff Current	(V <sub>CE</sub> = 50 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	1.0	mAdc
Collector Cutoff Current $ (V_{CE} = Rated \ V_{CEO}, \ V_{BE(off)} = 1.5 \ Vdc) $ $ (V_{CE} = Rated \ V_{CEO}, \ V_{BE(off)} = 1.5 \ Vdc, \ T_C = 150^{\circ}C) $		I <sub>CEX</sub>	_ _	0.5 5.0	mAdc
Emitter Cutoff Current	$(V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0)$	I <sub>EBO</sub>	-	2.0	mAdc
ON CHARACTERISTICS (Note 3)					_
DC Current Gain	$(I_C = 6.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc})$ $(I_C = 12 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc})$	h <sub>FE</sub>	750 100	18,000	_
Collector-Emitter Saturation Voltage	(I <sub>C</sub> = 6.0 Adc, I <sub>B</sub> = 24 mAdc) (I <sub>C</sub> = 12 Adc, I <sub>B</sub> = 120 mAdc)	V <sub>CE(sat)</sub>	_ _ _	2.0 3.0	Vdc
Base-Emitter Saturation Voltage	(I <sub>C</sub> = 12 Adc, I <sub>B</sub> = 120 mAdc)	V <sub>BE(sat)</sub>	-	4.0	Vdc
Base-Emitter On Voltage	$(I_C = 6.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc})$	V <sub>BE(on)</sub>	-	2.8	Vdc
DYNAMIC CHARACTERISTICS		•			
Magnitude of Common Emitter Small-Signal Short Circuit Forward Current Transfer Ratio ( $I_C = 5.0$ Adc, $V_{CE} = 3.0$ Vdc, $f = 1.0$ MHz)		h <sub>fe</sub>	4.0	_	MHz
Output Capacitance	(V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz)	C <sub>ob</sub>	-	500	pF
Small-Signal Current Gain	(I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 3.0 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	300	_	-

Indicates JEDEC Registered Data.
 Pulse test: Pulse Width = 300 μs, Duty Cycle = 2.0%.



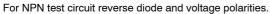


Figure 2. Switching Times Test Circuit

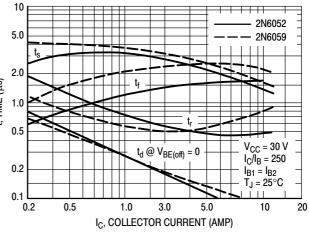


Figure 3. Switching Times

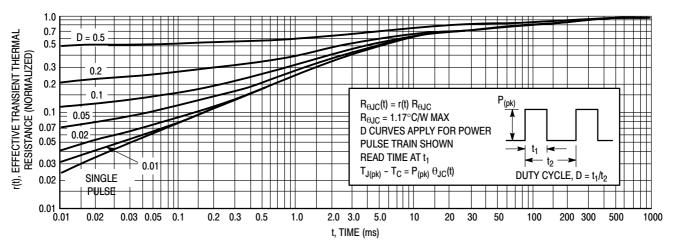


Figure 4. Thermal Response

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 5, and 6 is based on  $T_{J(pk)} = 200^{\circ} C$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 200^{\circ} C$ ;  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

# ACTIVE-REGION SAFE OPERATING AREA

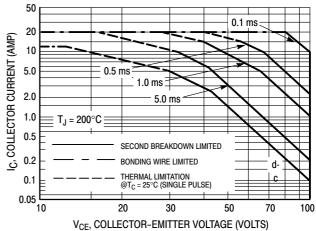


Figure 5.

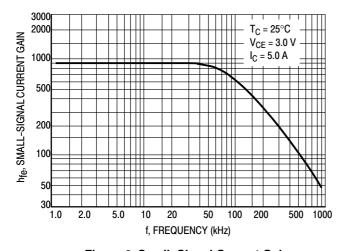


Figure 6. Small-Signal Current Gain

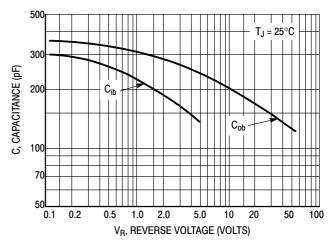


Figure 7. Capacitance

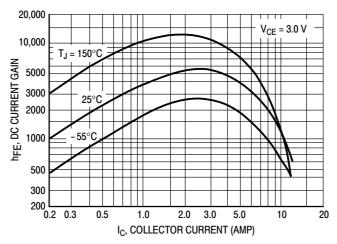


Figure 8. DC Current Gain

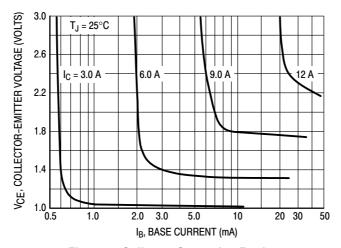


Figure 9. Collector Saturation Region

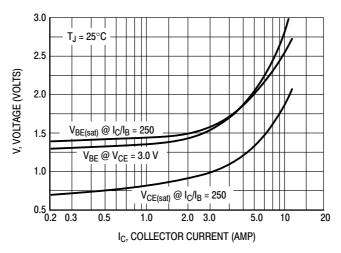
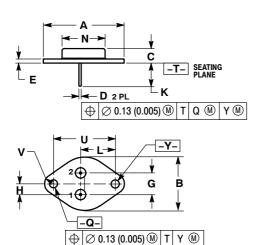


Figure 10. "On" Voltages

#### 2N6052

#### PACKAGE DIMENSIONS

**TO-204 (TO-3)**CASE 1-07
ISSUF 7



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
   VIA EM 1000
  - Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- ALL RULES AND NOTES ASSOCIATED WITH
   REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37	REF	
В		1.050		26.67	
C	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
E	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215 BSC		5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89 BSC		
N		0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187	BSC	30.15	BSC	
٧	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

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